



# UNITED STATES PATENT AND TRADEMARK OFFICE

UNITED STATES DEPARTMENT OF COMMERCE  
United States Patent and Trademark Office  
Address: COMMISSIONER OF PATENTS AND TRADEMARKS  
Washington, D.C. 20231  
www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/484,348	01/18/2000	Stanley E. Swirhun	36903/SAH/C715	9594

3017 7590 04/17/2003  
BARLOW, JOSEPHS & HOLMES, LTD.  
101 DYER STREET  
5TH FLOOR  
PROVIDENCE, RI 02903

EXAMINER

LOUIE, WAI SING

ART UNIT PAPER NUMBER

2814

DATE MAILED: 04/17/2003

Please find below and/or attached an Office communication concerning this application or proceeding.

**Office Action Summary**

Application No.

09/484,348

Applicant(s)

SWIRHUN ET AL.

Examiner

Wai-Sing Louie

Art Unit

2814

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

**Period for Reply**

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

**Status**

- 1) ☒ Responsive to communication(s) filed on 11 February 2003.
- 2a) ☒ This action is **FINAL**. 2b) ☐ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

**Disposition of Claims**

- 4) ☒ Claim(s) 22-39 is/are pending in the application.
- 4a) Of the above claim(s) \_\_\_\_\_ is/are withdrawn from consideration.
- 5) ☐ Claim(s) \_\_\_\_\_ is/are allowed.
- 6) ☒ Claim(s) 22-39 is/are rejected.
- 7) ☐ Claim(s) \_\_\_\_\_ is/are objected to.
- 8) ☐ Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

**Application Papers**

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on \_\_\_\_\_ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
- Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- 11) ☐ The proposed drawing correction filed on \_\_\_\_\_ is: a) ☐ approved b) ☐ disapproved by the Examiner.
- If approved, corrected drawings are required in reply to this Office action.
- 12) ☐ The oath or declaration is objected to by the Examiner.

**Priority under 35 U.S.C. §§ 119 and 120**

- 13) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some \* c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- \* See the attached detailed Office action for a list of the certified copies not received.
- 14) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).
- a) ☐ The translation of the foreign language provisional application has been received.
- 15) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

**Attachment(s)**

- 1) ☐ Notice of References Cited (PTO-892) 4) ☐ Interview Summary (PTO-413) Paper No(s). \_\_\_\_\_
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948) 5) ☐ Notice of Informal Patent Application (PTO-152)
- 3) ☐ Information Disclosure Statement(s) (PTO-1449) Paper No(s) \_\_\_\_\_ 6) ☐ Other: \_\_\_\_\_

Art Unit: 2814

## DETAILED ACTION

### *Claim Objections*

Claims 36-39 are objected. They are depending on canceled claims. Appropriate correction is required.

### *Double Patenting*

The nonstatutory double patenting rejection is based on a judicially created doctrine grounded in public policy (a policy reflected in the statute) so as to prevent the unjustified or improper timewise extension of the "right to exclude" granted by a patent and to prevent possible harassment by multiple assignees. See *In re Goodman*, 11 F.3d 1046, 29 USPQ2d 2010 (Fed. Cir. 1993); *In re Longi*, 759 F.2d 887, 225 USPQ 645 (Fed. Cir. 1985); *In re Van Ornum*, 686 F.2d 937, 214 USPQ 761 (CCPA 1982); *In re Vogel*, 422 F.2d 438, 164 USPQ 619 (CCPA 1970); and, *In re Thorington*, 418 F.2d 528, 163 USPQ 644 (CCPA 1969).

A timely filed terminal disclaimer in compliance with 37 CFR 1.321(c) may be used to overcome an actual or provisional rejection based on a nonstatutory double patenting ground provided the conflicting application or patent is shown to be commonly owned with this application. See 37 CFR 1.130(b).

Effective January 1, 1994, a registered attorney or agent of record may sign a terminal disclaimer. A terminal disclaimer signed by the assignee must fully comply with 37 CFR 3.73(b).

Claims 22-29, 31, and 33-34 are rejected under the judicially created doctrine of obviousness-type double patenting as being unpatentable over claims 1-18 of U.S. Patent No. 6,392,256. Although the conflicting claims are not identical, they are not patentably distinct from each other because

With regard to claim 22, US 6,392,256 discloses a monolithic optical transmitter and receiver pair comprising:

- A semiconductor substrate (claims 1 and 2);

Art Unit: 2814

- An optical transmitter formed on a discrete location (a portion) of the substrate (claims 1 and 4);
- An optical receiver formed laterally adjacent the optical transmitter, the optical receiver optically and electrically isolated from the optical transmitter (claims 1 and 6).

With regard to claim 23, US 6,392,256 discloses the optical receiver comprises a photodiode (claim 1).

With regard to claim 24, US 6,392,256 discloses the optical transmitter comprises a VCSEL having a plurality of layers (claim 1).

With regard to claim 25, US 6,392,256 discloses the VCSEL comprises an isolation region defining discrete areas of the active VCSEL layers and the inactive VCSEL layers (claims 6 and 11).

With regard to claim 26, US 6,392,256 discloses a means for disabling inactive VCSEL layers (claim 8).

With regard to claim 27, US 6,392,256 discloses the optical transmitter comprises:

- A first mirror layers formed on the substrate (claim 12);
- A first cladding layer formed on a top most first mirror layer (claim 12);
- An active region formed on said first cladding layer (claim 12);
- A second cladding layer formed on said active region (claim 12);
- A second mirror formed on said second cladding layer (claim 12).

With regard to claim 28, US 6,392,256 does not disclose the active region comprises at least one quantum well layer. However, a quantum well provides the carriers to generate and

Art Unit: 2814

recombine efficiently in the active region. Therefore, it would have been obvious to provide a quantum well in the active region.

With regard to claim 29, US 6,392,256 discloses a distributed p-type layer formed on the VCSEL (claim 3), but does not disclose the epitaxially grown distributed Bragg reflectors (BDR). However, it is common to form BDR in the VCSEL in order to have the reflective index for the device and to have the lattice matched with the other layers. Therefore, it would have been obvious to one with ordinary skill in the art to have the epitaxially grown distributed Bragg reflectors in order to have the lattice match and the correct reflective index.

With regard to claim 31, US 6,392,256 discloses optical receiver comprises:

- A distributed p-type layer formed on said VCSEL layers (claim 3);
- An intrinsic layer formed on said distributed p-type layer (claim 3);
- An n-type layer formed on said intrinsic layer (claim 3);
- A photodiode cathode contact formed on the n-type layer (claim 18);
- A photodiode anode formed on the topmost second mirror layer (claim 18).

With regard to claim 33, US 6,392,256 discloses a non-reflective coating on the optical receiver (claim 10).

With regard to claim 34, US 6,392,256 discloses a photodiodes formed on the semiconductor substrate (claim 11).

### ***Claim Rejections - 35 USC § 103***

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

Art Unit: 2814

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

Claims 22-26, 28-29, 32, and 34-35 are rejected under 35 U.S.C. 103(a) as being unpatentable over Olbright et al. (US 5,266,794).

With regard to claim 22, Olbright et al. disclose an integrated light emitting device and photo detector (col. 3, line 48 to col. 9, line 39 and fig. 9) comprising:

- A semiconductor substrate 200 (fig. 8);
- An optical transmitter 180 formed on a portion of the substrate 200 (fig. 8);
- An optical receiver 190 formed laterally adjacent the optical transmitter 180, the optical receiver 190 optically isolated from the optical transmitter 180 (fig 8).

Since the optical receiver 190 and the optical transmitter 180 are formed on an intrinsic GaAs substrate (fig. 8), therefore, it would have been obvious that the optical receiver 190 is electrically isolated from the optical transmitter 180.

With regard to claim 23, Olbright et al. disclose the optical receiver comprises a photodiode (col. 7, line 60).

With regard to claim 24, Olbright et al. disclose the optical transmitter comprises a VCSEL having a plurality of layers (fig. 8).

With regard to claim 25, Olbright et al. disclose the VCSEL comprises an isolation region defining discrete areas of the active VCSEL layers and the inactive VCSEL layers (fig. 8).

With regard to claims 26 and 32, Olbright et al. disclose the means for disabling inactive VCSEL layers is by electronically disabling the associated transmitters (col. 4, lines 20-24).

Art Unit: 2814

With regard to claim 28, Olbright et al. disclose the active region comprises a multiple quantum well layer (col. 8, line 14).

With regard to claim 29, Olbright et al. disclose the first and second mirrors are epitaxially grown distributed Bragg reflector layers (col. 8, line 13).

With regard to claim 34, Olbright et al. disclose a photodiodes formed on the semiconductor substrate (fig. 8).

With regard to claim 35, Olbright et al. disclose a monolithically integrated optical device having a VCSEL and an optical receiver. The receiver can comprise a metal-semiconductor-metal photodiode (Olbright col. 7, lines 59-61).

Claims 30-31 are rejected under 35 U.S.C. 103(a) as being unpatentable over Olbright et al. (US 5,266,794) in view of Hasnain et al. (US 5,136,603).

With regard to claim 30, Olbright et al. do not disclose a photodiode formed on a top most second mirror layer of the VCSEL layers. However, Hasnain et al. disclose forming a PIN photodiode formed on a top most second mirror layer of the VCSEL layers (Hasnain fig. 1). Hasnain et al. teach the photodiode is integrated with the VCSEL becomes a single mode operation and have low divergence optical output (Hasnain col. 1, lines 45-53). Therefore, it would have been obvious to one with ordinary skill in the art to modify Olbright's device with the teaching of Hasnain et al. to place the photodiode on the top most second mirror layer in order to operate the device as a single mode and have low divergence optical output.

With regard to claim 31, Olbright et al. disclose optical receiver comprises:

- A p-type layer 220a formed on a portion of the VCSEL layers (fig. 8);

Art Unit: 2814

- An n-type layer 230a (fig. 8);
- A photodiode cathode contact 330 formed on the n-type layer (fig. 8);
- Olbright et al. do not disclose an intrinsic layer. However, one with ordinary skill in the art would know a PN photodiode could be replaced by a PIN photodiode to improve the confinement of the carriers, such as the device disclosed by Hasnain et al., which has a PIN photodiode on top of the VCSEL. Therefore, it would have been obvious to have a PIN diode and having an intrinsic layer on top of the p-type layer 220a;
- A photodiode anode 320 formed on the p-type layer 220a (fig. 8). Although, the contact is not made on the top most second mirror layer, but the contact is made on a p-layer of the PIN photo detector to complete the circuit and, therefore, is considered as equivalent.

Claims 27 and 33 are rejected under 35 U.S.C. 103(a) as being unpatentable over Olbright et al. (US 5,266,794) in view of Lebby et al. (US 5,498,883).

With regard to claim 27, Olbright et al. disclose the optical transmitter comprises:

- A first mirror layers 270 formed on the substrate (fig. 8);
- An active region 250 formed on said first cladding layer (fig. 8);
- A second mirror 260 formed on said second cladding layer (fig. 8);
- Olbright et al. do not disclose a first and a second cladding layer formed on a top and beneath the active layer. However, cladding layers are used in VCSEL to improve the confinement of the carriers, which is common in the art, such as



Art Unit: 2814

disclose in Lebby et al. (Lebby col. 3, lines 24-43 and fig. 3). Therefore, it would have been obvious have cladding layers surrounding the active region.

With regard to claim 33, Olbright et al. do not disclose using a non-reflective coating. However, Lebby et al. disclose an anti-reflective coating is used in the device (fig. 3). Lebby et al. teach the anti-reflective coating suppresses lasing (Lebby col. 5, lines 27-30). Therefore, it would have been obvious to one with ordinary skill in the art to apply anti-reflective coating on the device. Doing so could control the light by suppress lasing.

### *Response to Arguments*

Applicant's arguments filed 9/18/02 have been fully considered but they are not persuasive.

- Applicant argues that US Patent No. 6, 392,256 discloses a stacked arrangement, where the optical receiver is stacked on top of the optical transmitter and the optical transmitter is formed over the entire surface of the substrate. However, US Patent No. 6, 392,256 discloses the VCSEL is formed on a discrete location of the substrate (claim 1) and the optical transmitter is isolated from the optical receiver (claim 6). Therefore, there is no teaching or suggestion in US Patent No. 6, 392,256 that the optical receiver is stacked on top of the optical transmitter and the optical transmitter is formed over the entire surface of the substrate.
- Applicant argues that the optical transmitter and the optical receiver in Olbright et al. work in interlocked relation by communication through the substrate and in particular by communication through the semiconductor substrate having logic

etched thereon. However, the substrate in Olbright's device is an intrinsic GaAs substrate (fig. 8), which is not a conductor. Therefore, the optical transmitter and optical receiver are isolated. There is nothing in the present claim to prevent the optical transmitter and the optical receiver from communication with each other through other means. Olbright et al. meet all limitations in claim 22.

- Applicant argues that there is no teaching either alone or in combination of these cited references (Olbright et al. and Hasnain et al.) that provides for the placement in close proximity of photodiode and VCSEL portion of the module through the use of a proton injected isolation region. However, Hasnain et al. utilize the upper p-type DBR mirror as the p-layer of the pin-junction and build the rest of the pin-junction structure on top of the p-type DBR mirror. Hasnain et al. teach the photodiode is integrated with the VCSEL becomes a single mode operation and have low divergence optical output (Hasnain col. 1, lines 45-53). This meets the claim limitation and the combination is proper.
- Applicant argues that the combination of Olbright et al. and Lebby et al. is improper and do not disclose the specific isolation limitations that restrict both electrical and optical interference. Examiner stated in the office action that cladding layers are used in VCSEL to improve the confinement of the carriers, which is common in the art. Lebby's device includes cladding layers around the active region. There are numerous references having cladding layers around an active region. Therefore, the combination is proper. In claims 27 and 33, there are

Art Unit: 2814

no limitations on restrict both electrical and optical interference. The argument is moot.

### *Conclusion*

**THIS ACTION IS MADE FINAL.** Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire **THREE MONTHS** from the mailing date of this action. In the event a first reply is filed within **TWO MONTHS** of the mailing date of this final action and the advisory action is not mailed until after the end of the **THREE-MONTH** shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than **SIX MONTHS** from the mailing date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Wai-Sing Louie whose telephone number is (703) 305-0474. The examiner can normally be reached on 7:30 AM to 4:00 PM.


If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael Fahmy can be reached on (703) 308-4918. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 308-7722 for regular communications and (703) 308-7722 for After Final communications.

Art Unit: 2814

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

wsl

April 8, 2003

  
LONG PHAM  
PRIMARY EXAMINER